
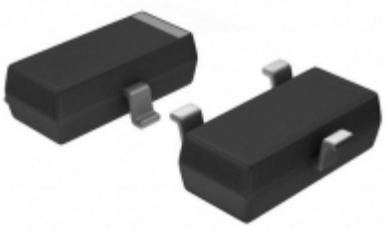
	<p><b>SI2367DS-T1-GE3</b></p>
	<p><b>Hersteller-Teilenummer:</b> SI2367DS-T1-GE3</p> <p><b>Hersteller / Marke:</b> Electro-Films (EFI) / Vishay</p> <p><b>Teil der Beschreibung:</b> MOSFET P-CH 20V 3.8A SOT-23</p> <p><b>Datenblätter:</b>  SI2367DS-T1-GE3.pdf</p> <p><b>RoHs Status:</b> Bleifrei / RoHS-konform</p> <p><b>Lagerzustand:</b> New original, 123035 pcs Stock Available.</p> <p><b>Liefern von:</b> Hong Kong</p> <p><b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI2367DS-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET P-CH 20V 3.8A SOT-23
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	123035 pcs Stock
detaillierte Beschreibung	P-Channel 20V 3.8A (Tc) 960mW (Ta), 1.7W (Tc)
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-236-3, SC-59, SOT-23-3
Supplier Device-Gehäuse	SOT-23-3 (TO-236)
Verlustleistung (max)	960mW (Ta), 1.7W (Tc)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	3.8A (Tc)
Rds On (Max) @ Id, Vgs	66 mOhm @ 2.5A, 4.5V
VGS (th) (Max) @ Id	1V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	23nC @ 8V
Eingabekapazität (Ciss) (Max) @ Vds	561pF @ 10V
Antriebsspannung (Max Rds On, Min Rds On)	1.8V, 4.5V
Vgs (Max)	±8V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI2367DS-T1-GE3-ND

SI2367DS-T1-GE3 ist neu im Original, Suche SI2367DS-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2367DS-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI2367DS-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p><b>SI2366DS-T1-GE</b> VISHAY SI2366DS-T1-GE VISHAY</p>	 <p><b>SI2369DS-T1-GE3</b> Vishay / Siliconix MOSFET P-CH 30V 7.6A TO-236</p>	 <p><b>SI2366DS-T1-GE3</b> Electro-Films (EFI) / Vishay MOSFET N-CH 30V 5.8A SOT-23</p>	 <p><b>SI2367DS-T1-E3</b> VISHAY SI2367DS-T1-E3 VISHAY</p>
 <p><b>SI2367DS-T1-GE3</b> Vishay / Siliconix MOSFET P-CH 20V 3.8A SOT-23</p>	 <p><b>SI2371EDS-T1-E3</b> Son SI2371EDS-T1-E3 Son</p>	 <p><b>SI2369DS-T1-GE3</b> Electro-Films (EFI) / Vishay MOSFET P-CH 30V 7.6A TO-236</p>	 <p><b>SI2371EDS-T1-GE3</b> Electro-Films (EFI) / Vishay MOSFET P-CH 30V 4.8A SOT-23</p>

heiße Teile

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SI2343CDS	SI2343CDS-T1-E3	SI2343CDS-T1-GE3	SI2343CDS-T1-GE3	SI2343DS-T1-E3
SI2343DS-T1-E3	SI2343DS-T1-GE3	SI2343DS-T1-GE3	SI2344DS-E3	SI2347DS-T1-GE3
SI2347DS-T1-GE3	SI2351DS-T1-E3	SI2351DS-T1-E3	SI2351DS-T1-GE3	SI2351DS-T1-GE3
SI2356DS-T1-GE3	SI2356DS-T1-GE3	SI2365EDS	SI2365EDS-T1-GE3	SI2365EDS-T1-GE3
SI2366DS-T1-E3	SI2366DS-T1-GE	SI2366DS-T1-GE3	SI2366DS-T1-GE3	SI2367DS-T1-E3
SI2367DS-T1-GE3	SI2369DS-T1-GE3	SI2369DS-T1-GE3	SI2371EDS-T1-GE3	SI2371EDS-T1-GE3
SI2372DS-T1-E3	SI2372DS-T1-GE3	SI2372DS-T1-GE3	SI2374DS-T1-GE3	SI2374DS-T1-GE3
SI2377DS-T1-GE3	SI2377EDS	SI2377EDS-T1-E3	SI2377EDS-T1-GE3	SI2377EDS-T1-GE3
SI2392ADS-T1-E3	SI2392ADS-T1-GE3	SI2392ADS-T1-GE3	SI2392DS-T1-GE3	SI2392DS-T1-GE3
SI2399CDS-T1-GE3	SI2399DS-T1-GE3	SI2399DS-T1-GE3	SI2400-BS	SI2400-FS

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